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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

### Complete if Known

Application Number	TBA
Filing Date	Herewith
First Named Inventor	Toru TANZAWA et al.
Group Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	001701.00240

### U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
<i>Qu</i>		5,570,315		Tanaka et al.	10/1996	
<i>Qu</i>		5,652,719		Tanaka et al.	07/1997	

### FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sub>3</sub>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

### OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>Qu</i>		M. BAUER, et al., "A Multilevel-cell 32Mb Flash Memory" 1995 IEEE International Solid-State Circuits Conference, pp. 132-133	
<i>Qu</i>		M. OHKAWA, et al., "A 98mm <sup>2</sup> 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell" 1996 IEEE International Solid-State Circuits Conference, pp. 36-37	
<i>Qu</i>		G. CAMPARDO, et al. "A 40mm <sup>2</sup> 3V 50MHz 64Mb 4-Level Cell NOR-Type Flash Memory", 2000 IEEE International Solid-State Circuits Conference, pg. 274	

Examiner Signature

*Vu Le*

Date Considered

*5/30/04*

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.